

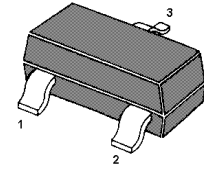
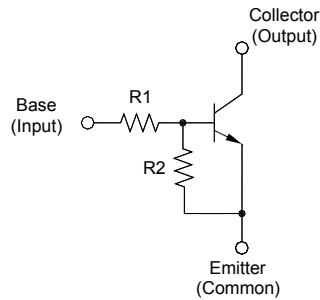
MMDTD231

NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	- 10 to + 12	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	39	-	-	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	0.5	μA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	3.8	mA
Collector Emitter Saturation Voltage at $I_C = 50\text{ mA}$, $I_B = 2.5\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Input on Voltage at $V_{CE} = 0.3\text{ V}$, $I_C = 20\text{ mA}$	$V_{I(on)}$	-	-	3	V
Input off Voltage at $V_{CE} = 5\text{ V}$, $I_C = 100\text{ }\mu\text{A}$	$V_{I(off)}$	0.5	-	-	V
Transition frequency at $V_{CE} = 10\text{ V}$, $I_E = 5\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz
Input Resistance	R_1	1.54	2.2	2.86	K Ω
Resistance Ratio	R_2 / R_1	0.8	1	1.2	-

